

# RJK1008DPN

N-Channel Power MOSFET High-Speed Switching Use

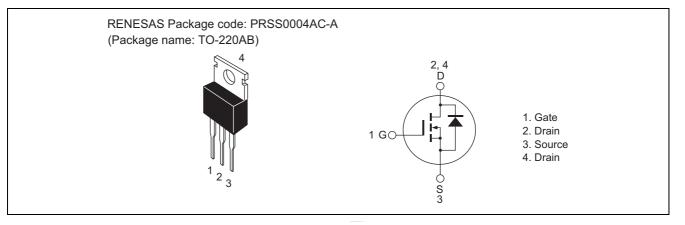
> REJ03G1627-0100 Rev.1.00 Mar 21, 2008

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# Features

- V<sub>DSS</sub>: 100 V
- $R_{DS(on)}$ : 11 m $\Omega$  (Max)
- I<sub>D</sub>: 80 A

# Outline



# Application

• Motor control, Lighting control, Solenoid control, DC-DC converter, etc.

# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	100	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	80	А
Drain peak current	I <sub>D (pulse)</sub>	160	А
Body-drain diode reverse drain current	I <sub>DR</sub>	80	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub>	160	А
Avalanche current	I <sub>AP</sub> <sup>Note2</sup>	40	А
Channel dissipation	Pch Note1	125	W
Channel to case thermal impedance	θch-c	1.0	°C/W
Channel temperature	Tch	150	٥C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Value at  $Tc = 25^{\circ}C$ 

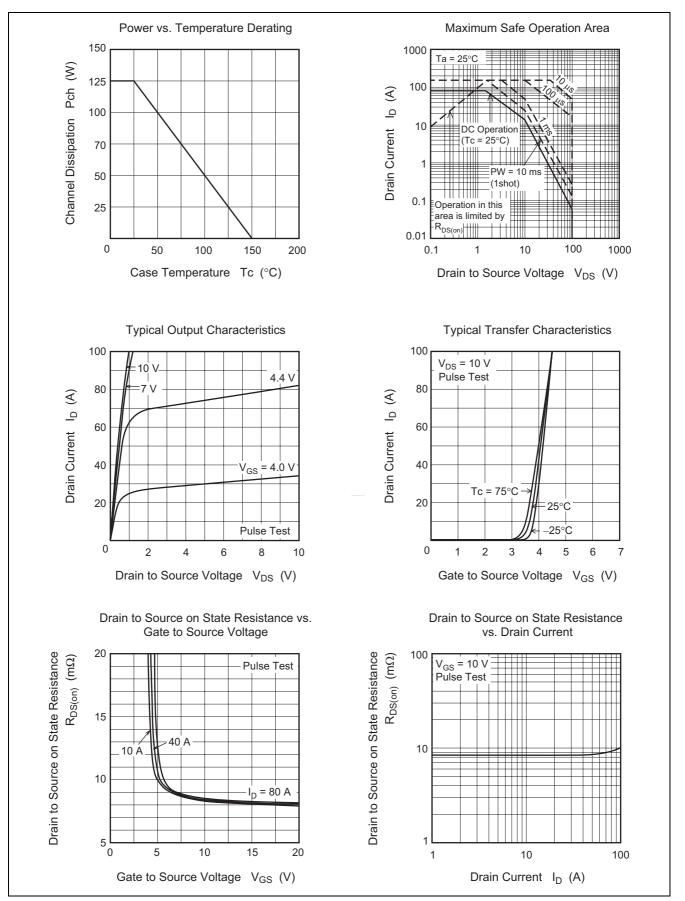
2. STch = 25°C, Tch  $\leq$  150°C, L = 100  $\mu H$ 

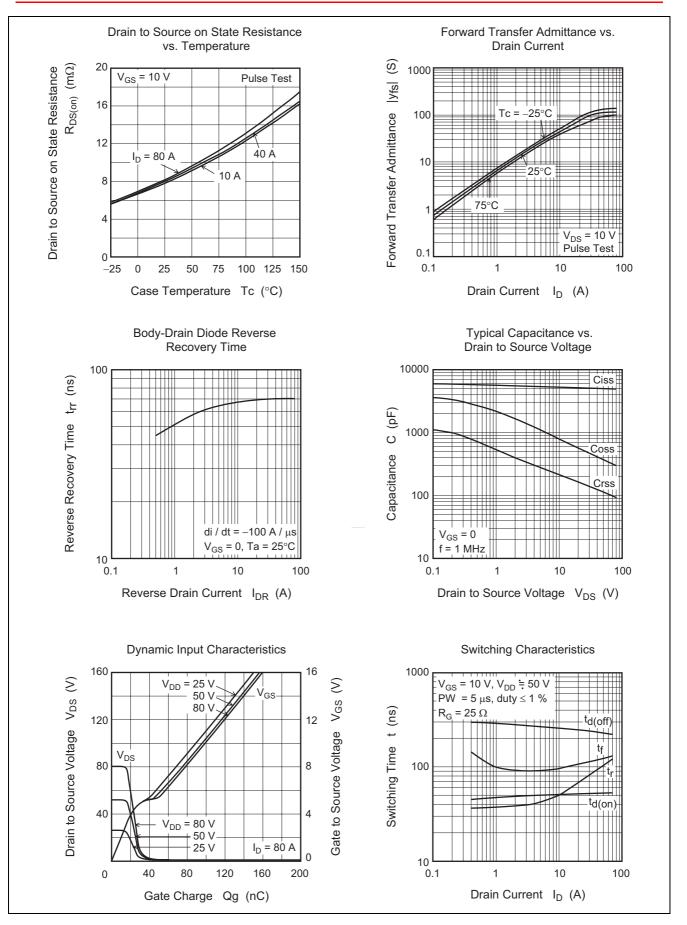
# **Electrical Characteristics**

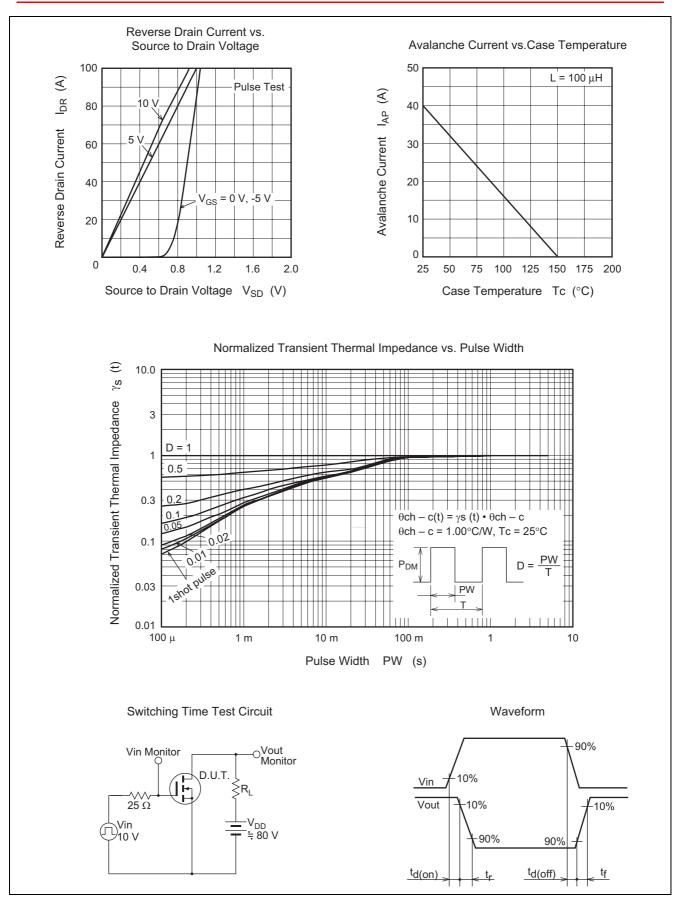
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	100	—	_	V	$I_{D} = 1 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	100	μΑ	$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	—	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state voltage	V <sub>DS(on)</sub>	_	0.34	0.44	V	$I_D = 40 \text{ A}, V_{GS} = 10 \text{ V}^{Note3}$
Static drain to source on state	R <sub>DS(on)</sub>	_	8.5	11	mΩ	$I_D = 40 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
resistance						
Input capacitance	Ciss	_	5200	_	рF	V <sub>DS</sub> = 10 V V <sub>GS</sub> = 0 f = 1 MHz
Output capacitance	Coss	_	820	—	pF	
Reverse transfer capacitance	Crss	_	220	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	52	_	ns	$V_{DD} = 50 V \\ I_D = 40 A \\ V_{GS} = 10 V \\ R_G = 25 \Omega$
Rise time	tr	_	100	_	ns	
Turn-off delay time	t <sub>d(off)</sub>	_	230		ns	
Fall time	t <sub>f</sub>	_	125		ns	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.9	1.5	V	$I_F = 40 \text{ A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	70	—	ns	$I_F = 80 \text{ A}, V_{GS} = 0$ di <sub>F</sub> /dt = 100 A/µs

Notes: 3. Pulse test

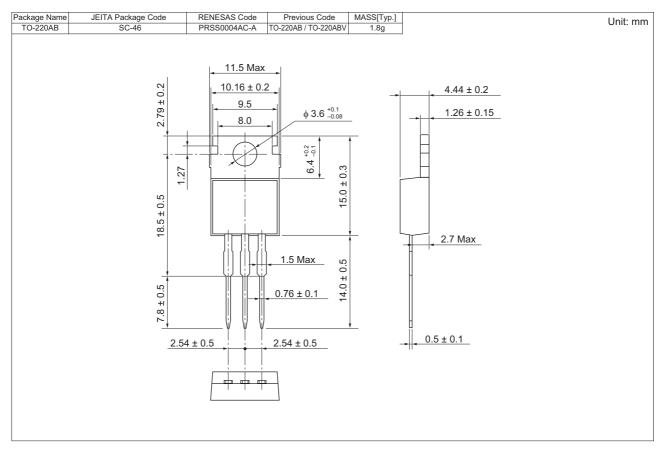
## **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK1008DPN-00-02	500 pcs	Box (Sack)

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